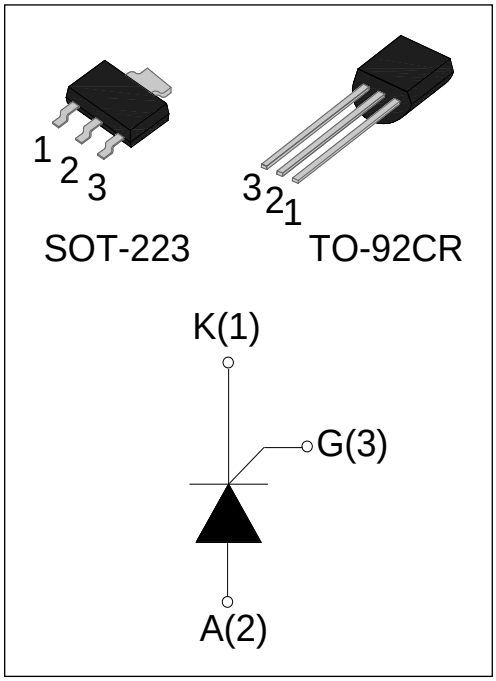
JX014 Series Sensitive gate SCRs

Rev.3.0

DESCRIPTION:

The JX014 SCR series provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1.25	A
I_{GT}	≤200	μA
V_{DRM} /V_{RRM}	900	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	℃
Operating junction temperature range		T_j	-40-110	℃
Repetitive peak off-state voltage		V_{DRM}	900	V
Repetitive peak reverse voltage		V_{RRM}	900	V
RMS on-state current	TO-92CR (T_C=50℃)	$I_{T(RMS)}$	1.25	A
	SOT-223 (T_C=75℃)			
Non repetitive surge peak on-state current (tp=10ms)		I_{TSM}	20	A
I^2t value for fusing (tp=10ms)		I^2t	2	A^2s
Critical rate of rise of on-state current		dI/dt	50	A/μs
Peak gate current (tp=20μs, Tj=110℃)		I_{GM}	0.2	A
Peak gate power (tp=20μs, Tj=110℃)		P_{GM}	0.5	W
Average gate power dissipation(T_j=110℃)		$P_{G(AV)}$	0.1	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	V_D=V_{DRM} T_j=110℃	0.2	-	-	V
I_L	I_G=1.2 I_{GT}	-	-	5	mA
I_H	I_T=0.05A	-	-	4	mA
dV/dt	V_D=2/3V_{DRM} T_j=110℃ R_{GK}=1KΩ	50	-	-	V/μs

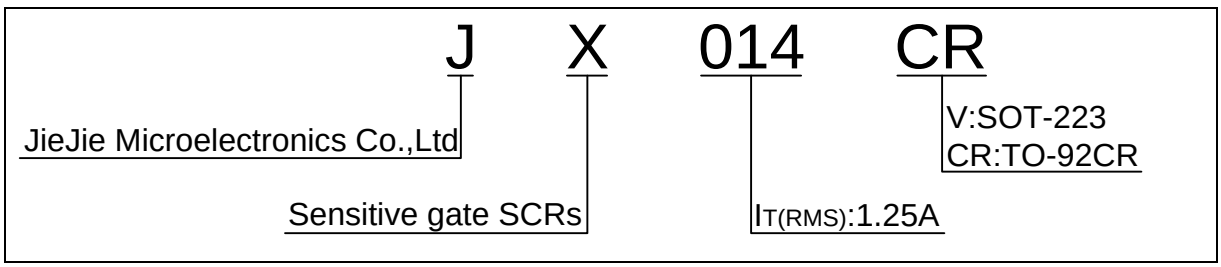
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM}=4A tp=380μs	T_j=25℃	1.5	V
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=110℃	100	μA

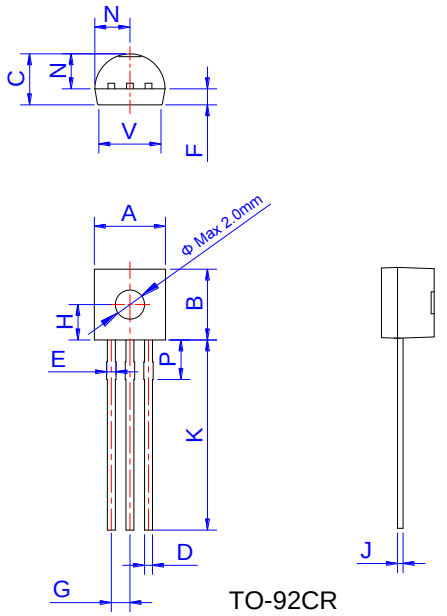
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-92CR	57	℃/W
		SOT-223	30	

ORDERING INFORMATION

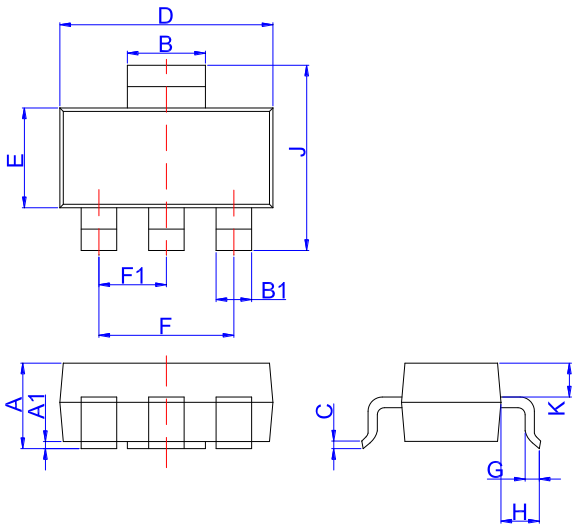


PACKAGE MECHANICAL DATA



TO-92CR

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.56		5.00	0.179		0.197
B	4.56		5.00	0.179		0.197
C	3.30		3.60	0.130		0.142
D	0.50		0.60	0.020		0.024
E	0.60		0.80	0.024		0.032
F	-	1.1	-		0.043	
G	-	1.27	-	-	0.050	-
H	-	2.43	-	-	0.096	-
J	0.36		0.50	0.014		0.020
K	11.50	13.00	14.20	0.453	0.512	0.559
N	2.04		2.66	0.080		0.105
P	2.50		2.90	0.098		0.114
V	-		4.3	-		0.169



SOT-223

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0	0.06	0.10	0	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K	0.8	0.9	1.0	0.031	0.035	0.039

FIG.1 Maximum power dissipation versus RMS on-state current

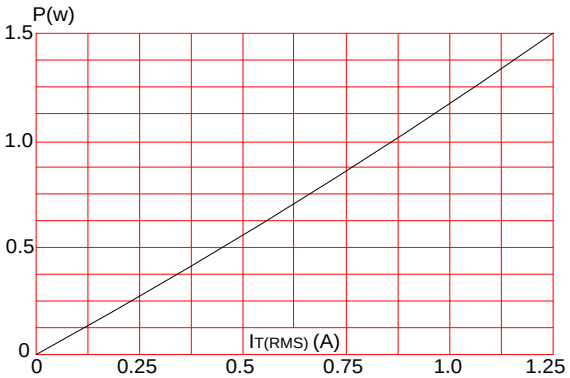


FIG.2: RMS on-state current versus case temperature

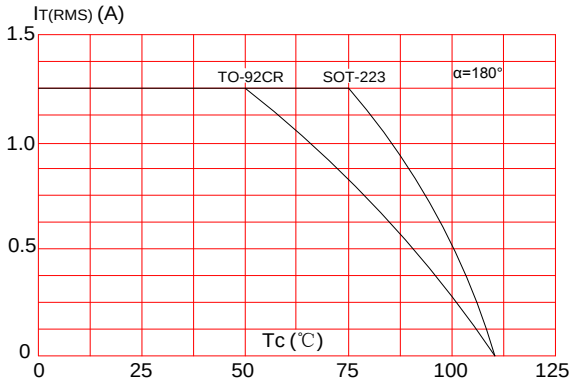


FIG.3: Surge peak on-state current versus number of cycles

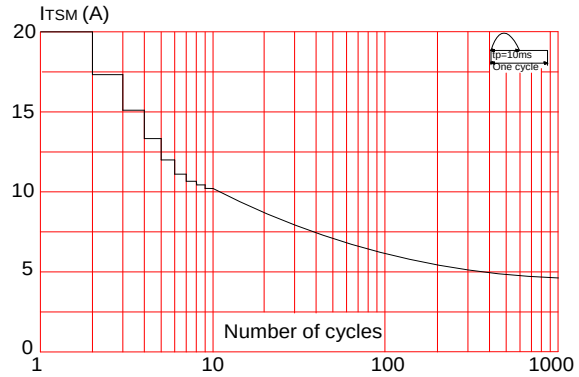


FIG.4: On-state characteristics (maximum values)

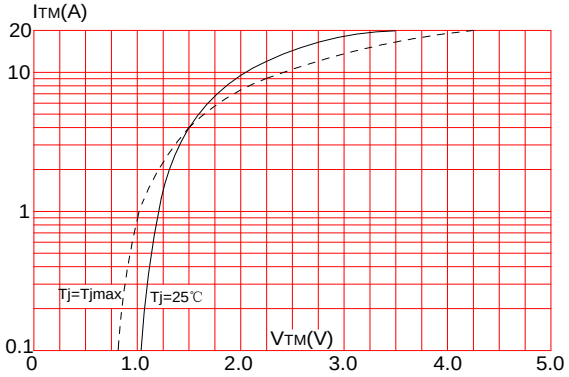


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<10ms, and corresponging value of I^2t (dI/dt < 50A/μs)

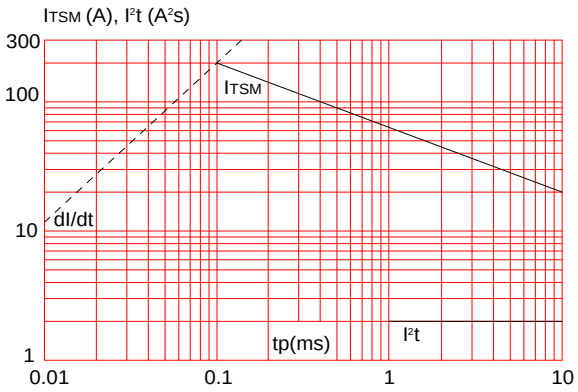
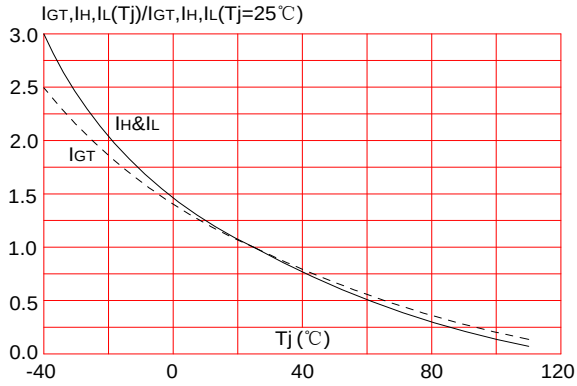


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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